

BSB10NH025SK1

N-Channel Power MOSFET

100 V, 280 A, 2.5 mΩ

Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency. It has been optimized for low gate charge, low $R_{DS(on)}$, fast switching speed.

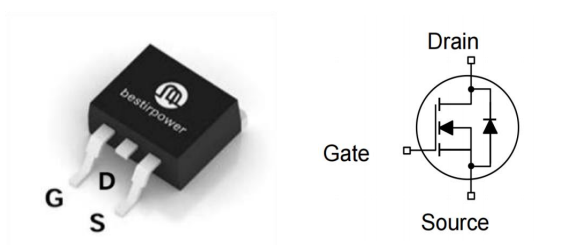
Features

BV_{DSS}	I_D	$R_{DS(on),max}$	$Q_{rr,typ}$
100 V	280 A	2.5 mΩ	180 nC

- $R_{DS(on),MAX}=2.5m\Omega@V_{gs}=10V$
- Low gate Charge (typical 185.5nC)
- Low C_{rss} (typical 63pF)
- Low On-Resistance
- Excellent FoM(figure of merit)
- 100% UIS and Rg tested

Applications

- DC/DC Converter
- Motor Driver
- Uninterruptible Power Supplies



Absolute Maximum Ratings ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		100	V
V_{GSS}	Gate to Source Voltage		± 20	V
I_D	Continuous Drain Current, ($T_C = 25^\circ\text{C}$) ¹⁾		280	A
	Continuous Drain Current, ($T_C = 100^\circ\text{C}$) ¹⁾		196	
I_{DM}	Drain Current (2)	Pulsed	1120	A
E_{AS}	Single Pulsed Avalanche Energy (3)		1551	mJ
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	357	W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	35	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	-	-	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$	-	2	2.5	mΩ

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V},$ $f = 1.0\text{ MHz}$	-	11389	-	pF
C_{oss}	Output Capacitance		-	1500	-	pF
C_{rss}	Reverse transfer capacitance		-	63	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	$V_{GS} = 10\text{ V}, V_{DD} = 50\text{ V}$ $I_D = 40\text{ A}$	-	185.5	-	nC
Q_{gs}	Gate to Source Charge		-	55	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	53.3	-	nC
R_G	Gate Resistance	$f = 1\text{ MHz}$	-	1.6	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{ V}, V_{DD} = 50\text{ V}$ $R_G = 3\text{ }\Omega, I_D = 40\text{ A}$	-	85	-	ns
t_r	Turn-On Rise Time		-	137	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	92	-	ns
t_f	Turn-Off Fall Time		-	98	-	ns

Source-Drain Diode Characteristics

I_S	Continuous Diode Forward Current	$T_J = 25^\circ\text{C}, I_S = 40\text{ A}, V_{GS} = 0\text{ V}$	-	280	-	A
$I_{S\text{ pulse}}$	Diode Pulsed Current ²⁾		-	1120	-	
V_{SD}	Diode Forward Voltage	$T_J = 25^\circ\text{C}, I_S = 40\text{ A}, V_{GS} = 0\text{ V}$	-	0.83	1.4	V
t_{rr}	Reverse Recovery Time	$I_F = 40\text{ A}, diF/dt = 100\text{ A/us}$	-	79	-	ns
Q_{rr}	Reverse Recovery Charge		-	180	-	nC

Notes

- 1) Limited by maximum junction temperature.
- 2) Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3) $L = 0.5\text{ mH}$, $R_G = 25\text{ }\Omega$, $V_{GS} = 10\text{ V}$, $V_{DD} = 50\text{ V}$, Start $T_J = 25^\circ\text{C}$.

Typical Performance Characteristics

Figure 1. Transient Thermal Impedance

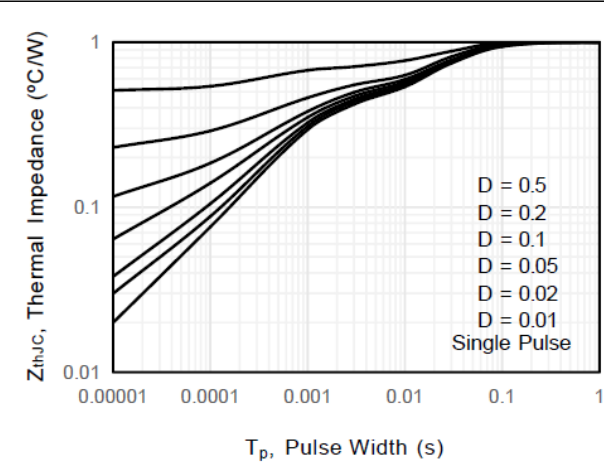


Figure 2 . Safe Operation Area

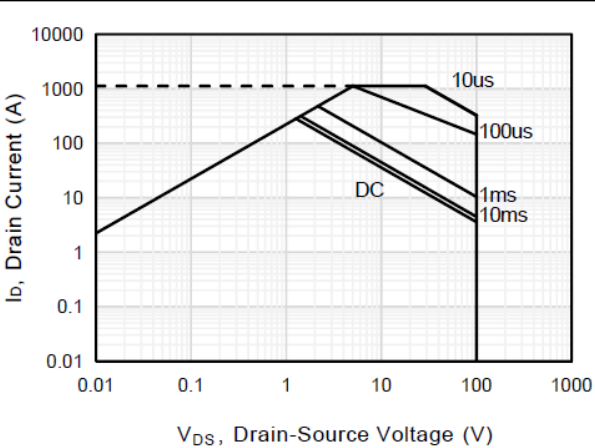


Figure 3 . Output Characteristics

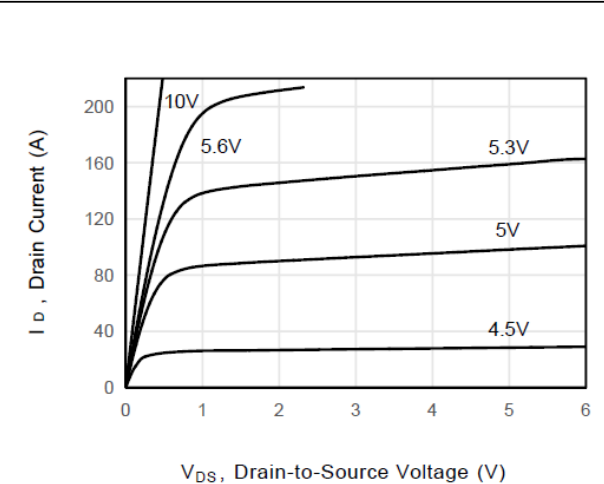


Figure 4 . Transfer Characteristics

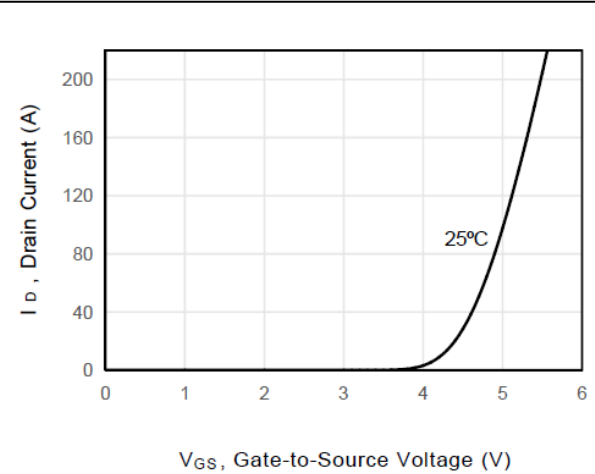


Figure 5 . On-Resistance vs Drain Current

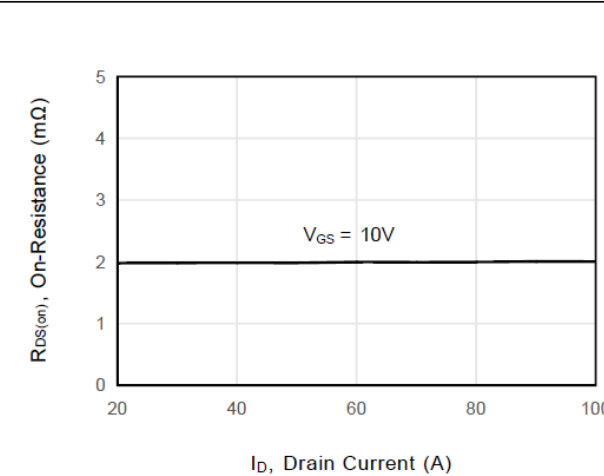
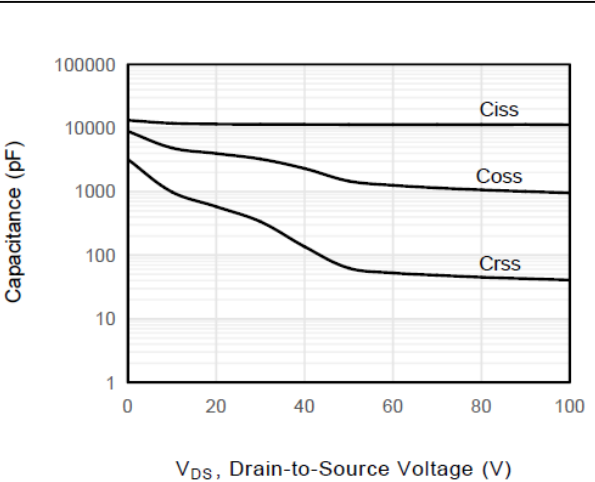


Figure 6 . Capacitance



Typical Performance Characteristics

Figure 7 . Gate Charge

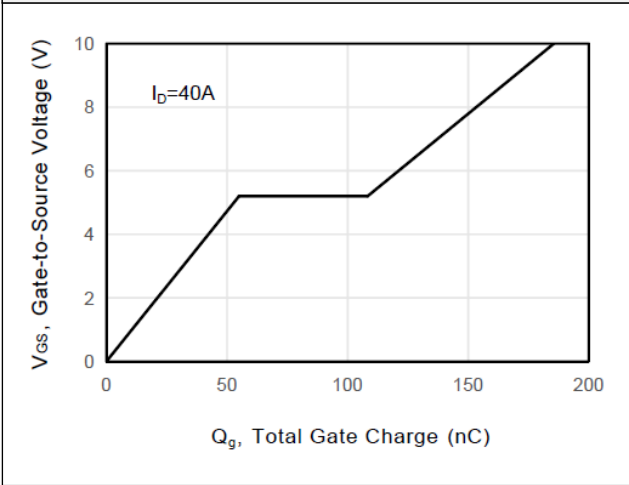


Figure 8 . Body Diode Forward Voltage

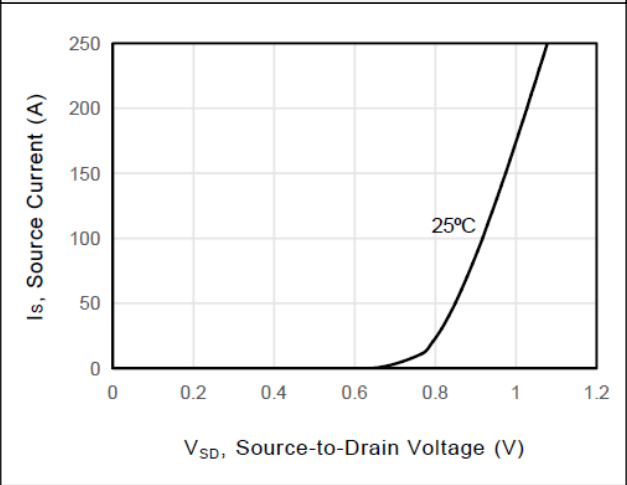


Figure 9. Breakdown Voltage vs Junction Temperature

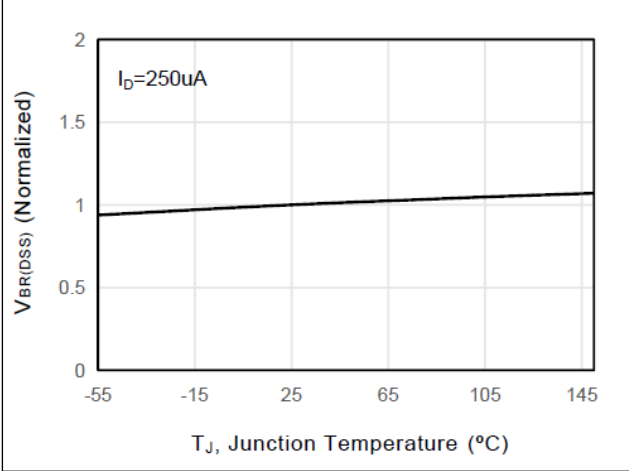


Figure 10. On-Resistance vs Temperature

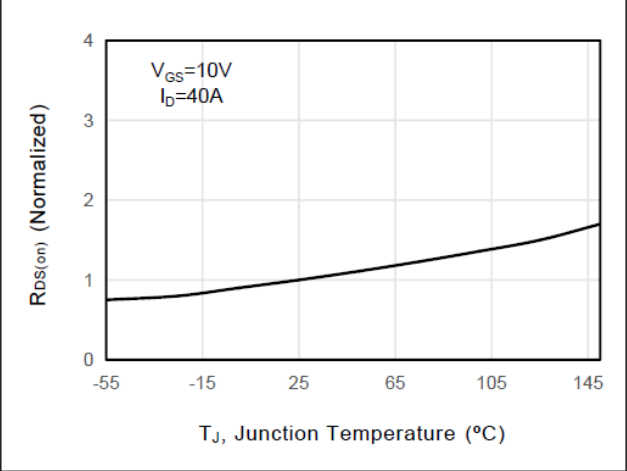
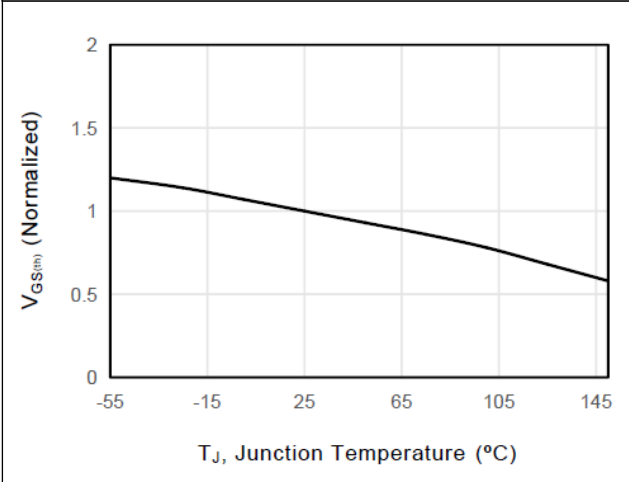


Figure 11. $V_{GS(th)}$ vs Junction Temperature



Test Circuits

Figure 12: Gate Charge Test Circuit and Waveform

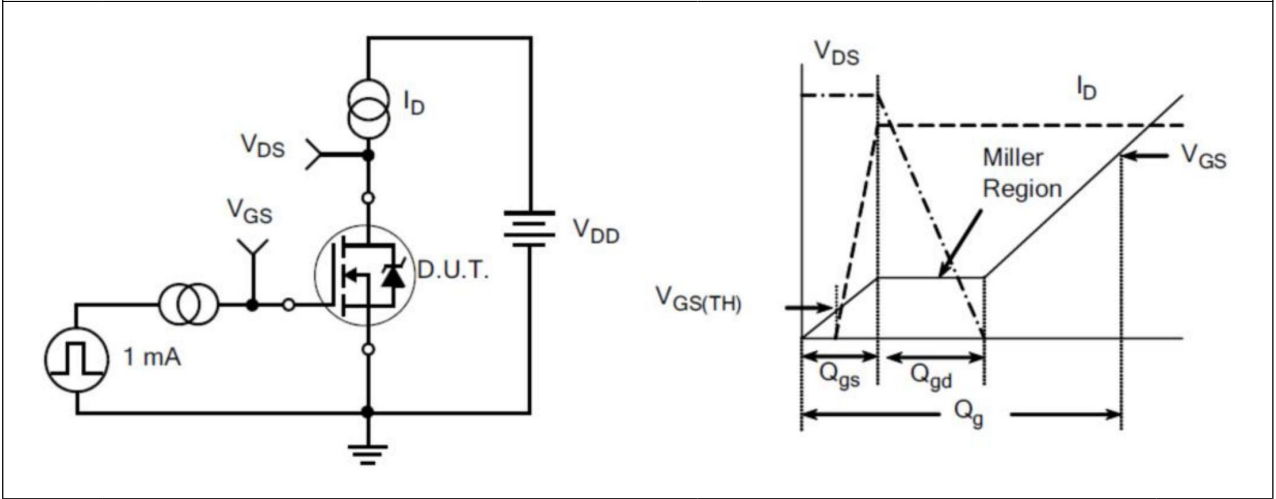


Figure 13: Resistive Switching Test Circuit and Waveform

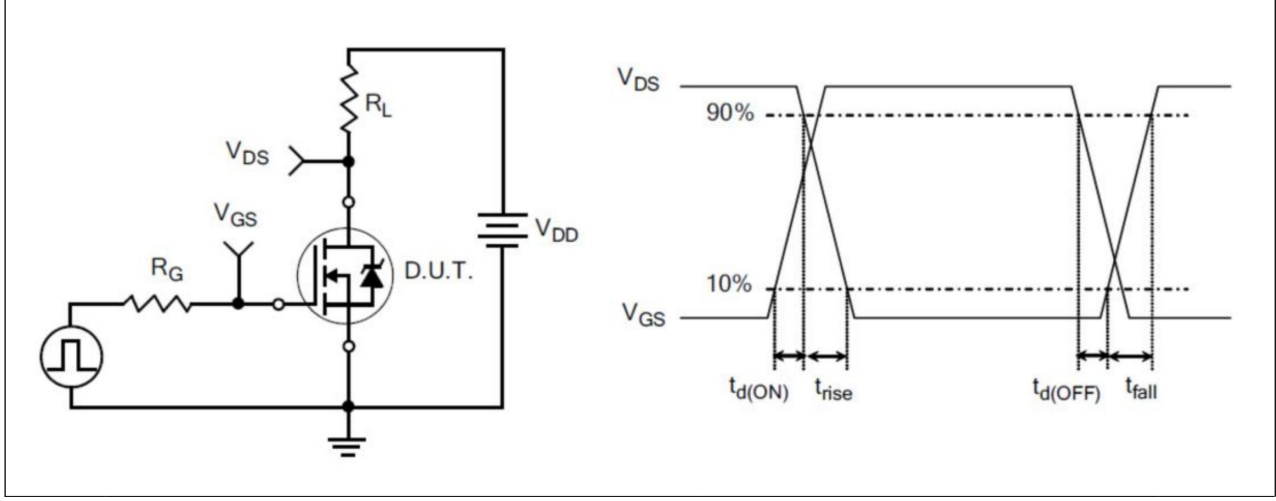
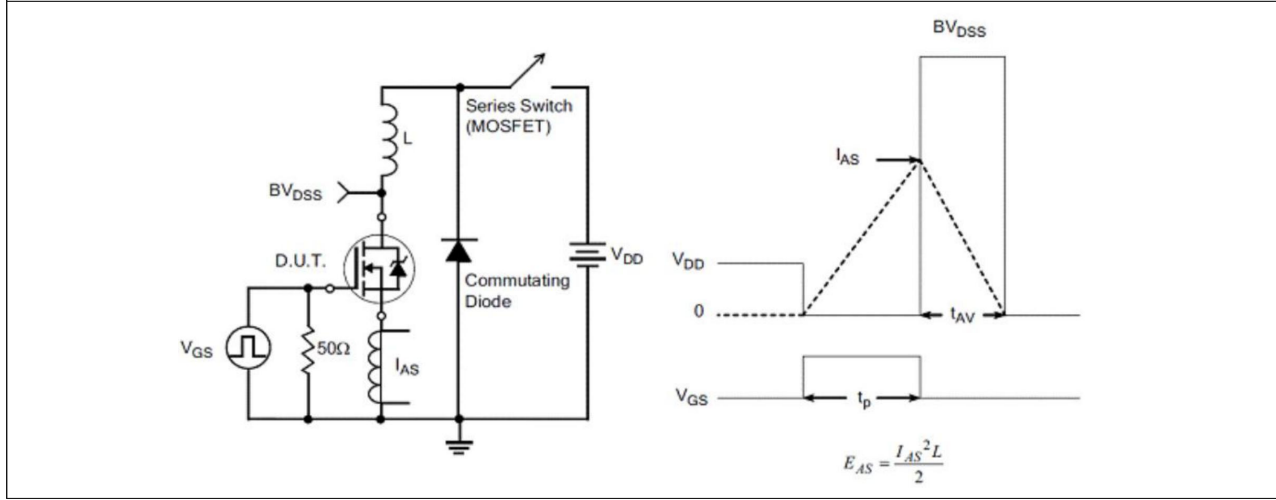
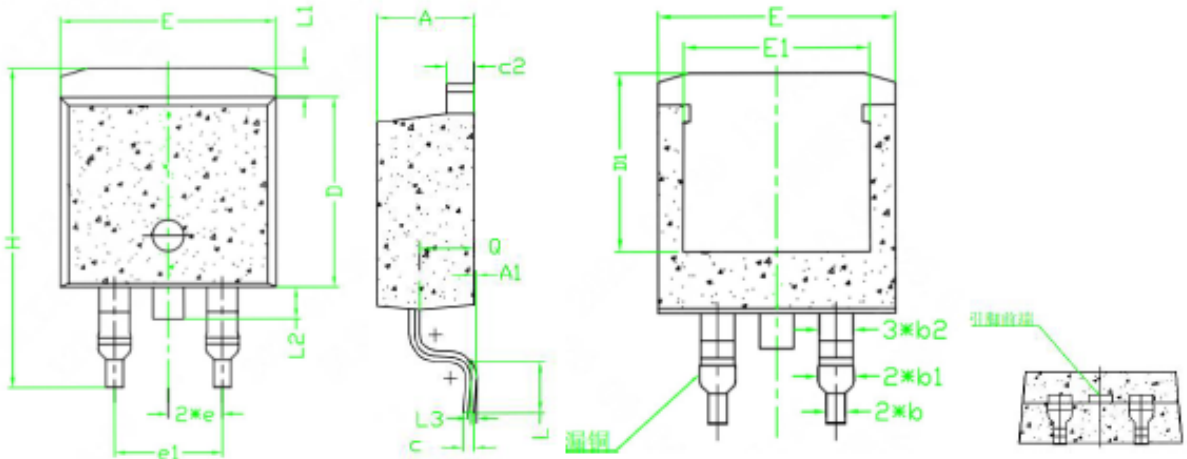


Figure 14: Unclamped Inductive Switching Test Circuit and Waveform



Package Outlines
D²PAK



SYMBOL	SIZE		
	MIN	NOM	MAX
A	4.40	4.50	4.70
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
C		0.50	
c2		1.27	1.30
D	9.1	9.2	9.25
D1	6.86	7.65	
E	9.8	10	10.2
E1	7.9	8	8.1
e	2.54BSC		
e1	5.08BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36REF		
L2	1.50REF		

* Dimensions in millimeters

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
BSB10NH025SK1	BSB10NH025SK1	D ² PAK	Tape & Reel	1000 units

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